



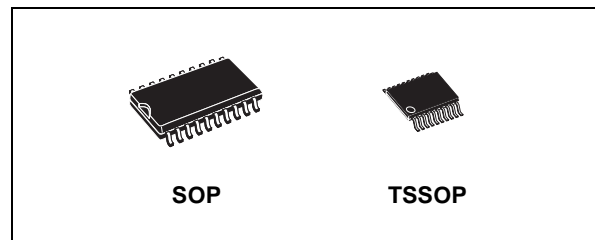
74LCX573

OCTAL D-TYPE LATCH NON-INVERTING (3-STATE) WITH 5V TOLERANT INPUTS AND OUTPUTS

- 5V TOLERANT INPUTS AND OUTPUTS
- HIGH SPEED :
 $t_{PD} = 8.0 \text{ ns (MAX.)}$ at $V_{CC} = 3V$
- POWER DOWN PROTECTION ON INPUTS AND OUTPUTS
- SYMMETRICAL OUTPUT IMPEDANCE:
 $|I_{OH}| = I_{OL} = 24\text{mA (MIN)}$ at $V_{CC} = 3V$
- PCI BUS LEVELS GUARANTEED AT 24 mA
- BALANCED PROPAGATION DELAYS:
 $t_{PLH} \approx t_{PHL}$
- OPERATING VOLTAGE RANGE:
 $V_{CC(OPR)} = 2.0V \text{ to } 3.6V$ (1.5V Data Retention)
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 573
- LATCH-UP PERFORMANCE EXCEEDS 500mA (JESD 17)
- ESD PERFORMANCE:
HBM > 2000V (MIL STD 883 method 3015);
MM > 200V

DESCRIPTION

The 74LCX573 is a low voltage CMOS OCTAL D-TYPE LATCH with 3 STATE OUTPUT NON-INVERTING fabricated with sub-micron silicon gate and double-layer metal wiring C²MOS technology. It is ideal for low power and high speed 3.3V applications; it can be interfaced to 5V signal environment for both inputs and outputs. These 8 bit D-Type latch are controlled by a latch



ORDER CODES

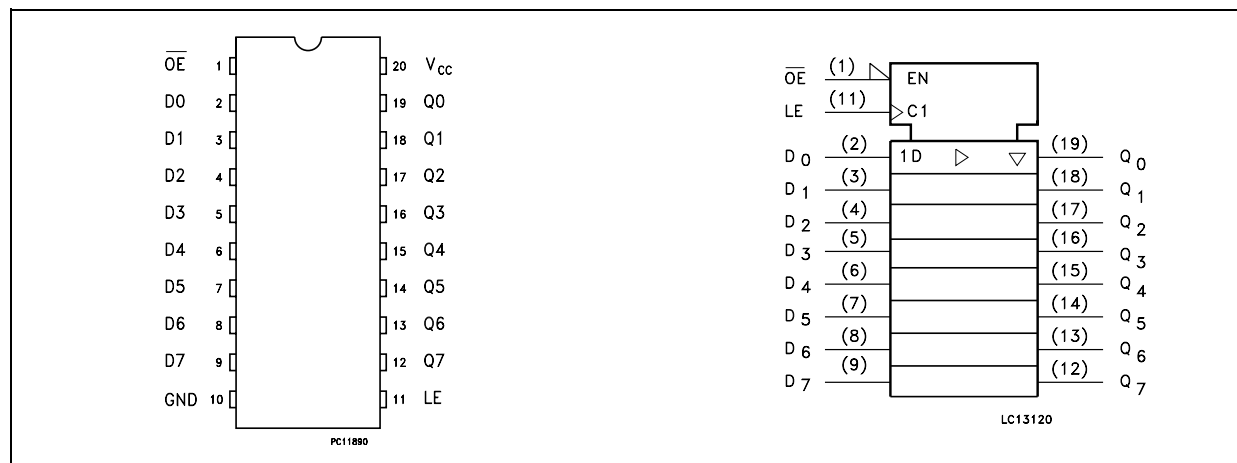
PACKAGE	TUBE	T & R
SOP	74LCX573M	74LCX573MTR
TSSOP		74LCX573TTR

enable input (LE) and an output enable input (\overline{OE}). While the LE inputs is held at a high level, the Q outputs will follow the data input. When the LE is taken low, the Q outputs will be latched at the logic level of D input data. While the (\overline{OE}) input is low, the 8 outputs will be in a normal logic state (high or low logic level) and while (\overline{OE}) is in high level, the outputs will be in a high impedance state.

It has same speed performance at 3.3V than 5V AC/ACT family, combined with a lower power consumption.

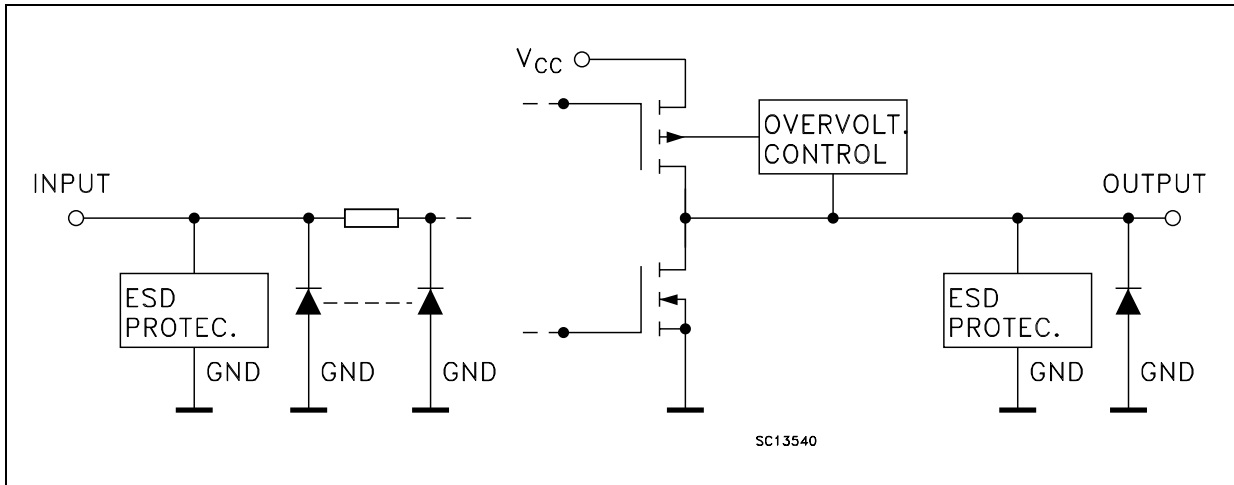
All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



74LCX573

INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1	OE	3 State Output Enable Input (Active LOW)
2, 3, 4, 5, 6, 7, 8, 9	D0 to D7	Data Inputs
12, 13, 14, 15, 16, 17, 18, 19	Q0 to Q7	3-State Latch Outputs
11	LE	Latch Enable Input
10	GND	Ground (0V)
20	V _{CC}	Positive Supply Voltage

TRUTH TABLE

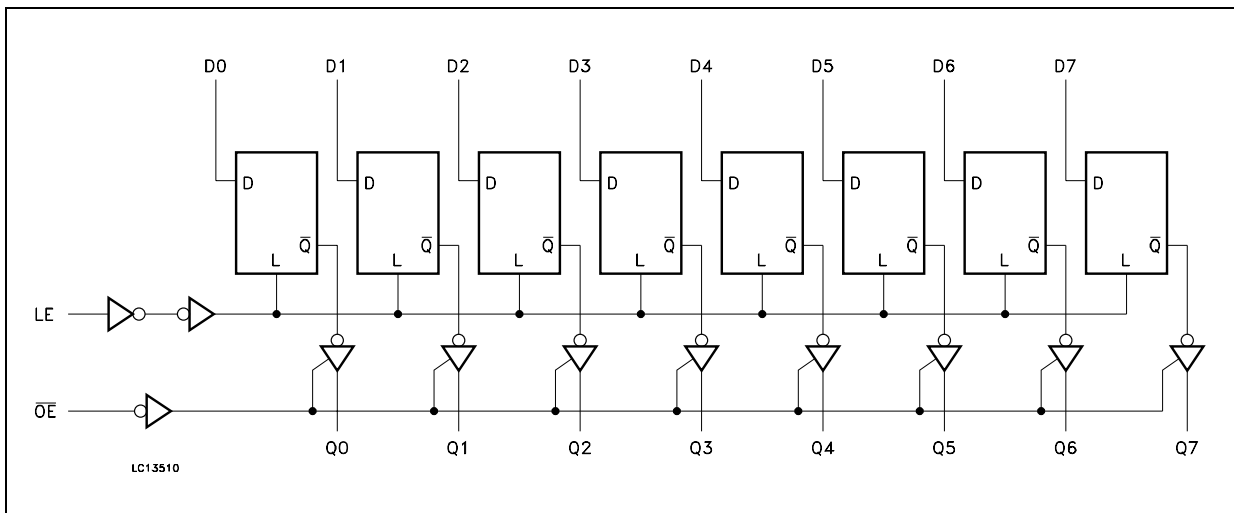
INPUT			OUTPUT
\overline{OE}	LE	D	Q
H	X	X	Z
L	L	X	NO CHANGE*
L	H	L	L
L	H	H	H

X : Don't Care

Z : High Impedance

* : Q Outputs are latched at the time when the LE input is taken LOW.

LOGIC DIAGRAM



This logic diagram has not been used to estimate propagation delays

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	-0.5 to +7.0	V
V_I	DC Input Voltage	-0.5 to +7.0	V
V_O	DC Output Voltage (OFF State)	-0.5 to +7.0	V
V_O	DC Output Voltage (High or Low State) (note 1)	-0.5 to $V_{CC} + 0.5$	V
I_{IK}	DC Input Diode Current	- 50	mA
I_{OK}	DC Output Diode Current (note 2)	- 50	mA
I_O	DC Output Current	± 50	mA
I_{CC}	DC Supply Current per Supply Pin	± 100	mA
I_{GND}	DC Ground Current per Supply Pin	± 100	mA
T_{stg}	Storage Temperature	-65 to +150	°C
T_L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied

1) I_O absolute maximum rating must be observed

2) $V_O < GND$

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage (note 1)	2.0 to 3.6	V
V_I	Input Voltage	0 to 5.5	V
V_O	Output Voltage (OFF State)	0 to 5.5	V
V_O	Output Voltage (High or Low State)	0 to V_{CC}	V
I_{OH}, I_{OL}	High or Low Level Output Current ($V_{CC} = 3.0$ to $3.6V$)	± 24	mA
I_{OH}, I_{OL}	High or Low Level Output Current ($V_{CC} = 2.7V$)	± 12	mA
T_{op}	Operating Temperature	-55 to 125	°C
dt/dv	Input Rise and Fall Time (note 2)	0 to 10	ns/V

1) Truth Table guaranteed: 1.5V to 3.6V

2) V_{IN} from 0.8V to 2V at $V_{CC} = 3.0V$

DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value				Unit
		V _{CC} (V)		-40 to 85 °C		-55 to 125 °C		
				Min.	Max.	Min.	Max.	
V _{IH}	High Level Input Voltage	2.7 to 3.6		2.0		2.0		V
V _{IL}	Low Level Input Voltage					0.8		0.8
V _{OH}	High Level Output Voltage	2.7 to 3.6	I _O =-100 μA	V _{CC} -0.2		V _{CC} -0.2		V
		2.7	I _O =-12 mA	2.2		2.2		
		3.0	I _O =-18 mA	2.4		2.4		
			I _O =-24 mA	2.2		2.2		
V _{OL}	Low Level Output Voltage	2.7 to 3.6	I _O =100 μA		0.2		0.2	V
		2.7	I _O =12 mA		0.4		0.4	
		3.0	I _O =16 mA		0.4		0.4	
			I _O =24 mA		0.55		0.55	
I _I	Input Leakage Current	2.7 to 3.6	V _I = 0 to 5.5V		± 5		± 5	μA
I _{off}	Power Off Leakage Current	0	V _I or V _O = 5.5V		10		10	μA
I _{OZ}	High Impedance Output Leakage Current	2.7 to 3.6	V _I = V _{IH} or V _{IL} V _O = 0 to V _{CC}		± 5		± 5	μA
I _{CC}	Quiescent Supply Current	2.7 to 3.6	V _I = V _{CC} or GND		10		10	μA
			V _I or V _O = 3.6 to 5.5V		± 10		± 10	
ΔI _{CC}	I _{CC} incr. per Input	2.7 to 3.6	V _{IH} = V _{CC} - 0.6V		500		500	μA

DYNAMIC SWITCHING CHARACTERISTICS

Symbol	Parameter	Test Condition		Value			Unit
		V _{CC} (V)		T _A = 25 °C			
				Min.	Typ.	Max.	
V _{OLP}	Dynamic Low Level Quiet Output (note 1)	3.3	C _L = 50pF V _{IL} = 0V, V _{IH} = 3.3V		0.8		V
V _{OLV}					-0.8		

1) Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH to LOW or LOW to HIGH. The remaining output is measured in the LOW state.

AC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Condition				Value				Unit
		V _{CC} (V)	C _L (pF)	R _L (Ω)	t _s = t _r (ns)	-40 to 85 °C		-55 to 125 °C		
						Min.	Max.	Min.	Max.	
t _{PLH} t _{PHL}	Propagation Delay Time (Dn to Qn)	2.7	50	500	2.5	1.5	9.0	1.5	9.0	ns
		3.0 to 3.6				1.5	8.0	1.5	8.0	
t _{PLH} t _{PHL}	Propagation Delay Time (LE to Qn)	2.7	50	500	2.5	1.5	9.5	1.5	9.5	ns
		3.0 to 3.6				1.5	8.5	1.5	8.5	
t _{PZL} t _{PZH}	Output Enable Time to HIGH and LOW level	2.7	50	500	2.5	1.5	9.5	1.5	9.5	ns
		3.0 to 3.6				1.5	8.5	1.5	8.5	
t _{PLZ} t _{PHZ}	Output Disable Time from HIGH to LOW level	2.7	50	500	2.5	1.5	8.5	1.5	8.5	ns
		3.0 to 3.6				1.5	7.5	1.5	7.5	
t _S	Set-Up Time, HIGH or LOW level (Dn to LE)	2.7	50	500	2.5	2.5		2.5		ns
		3.0 to 3.6				2.5		2.5		
t _H	Hold Time, HIGH or LOW level (Dn to LE)	2.7	50	500	2.5	1.5		1.5		ns
		3.0 to 3.6				1.5		1.5		
t _W	LE Pulse Width, HIGH	2.7	50	500	2.5	3.3		3.3		ns
		3.0 to 3.6				3.3		3.3		
t _{OSLH} t _{OSHL}	Output To Output Skew Time (note1, 2)	3.0 to 3.6	50	500	2.5		1.0		1.0	ns

1) Skew is defined as the absolute value of the difference between the actual propagation delay for any two outputs of the same device switching in the same direction, either HIGH or LOW (t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|)

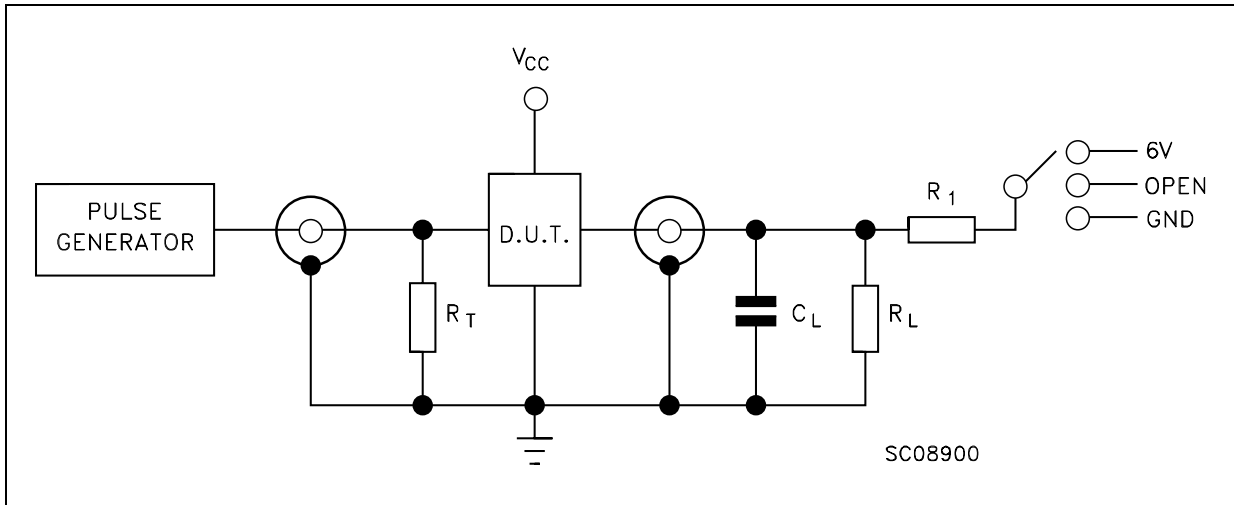
2) Parameter guaranteed by design

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Condition		Value			Unit
		V _{CC} (V)		T _A = 25 °C			
				Min.	Typ.	Max.	
C _{IN}	Input Capacitance	3.3	V _{IN} = 0 to V _{CC}		6		pF
C _{OUT}	Output Capacitance	3.3	V _{IN} = 0 to V _{CC}		12		pF
C _{PD}	Power Dissipation Capacitance (note 1)	3.3	f _{IN} = 10MHz V _{IN} = 0 or V _{CC}		25		pF

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. I_{CC(oper)} = C_{PD} × V_{CC} × f_{IN} + I_{CC/8} (per latch)

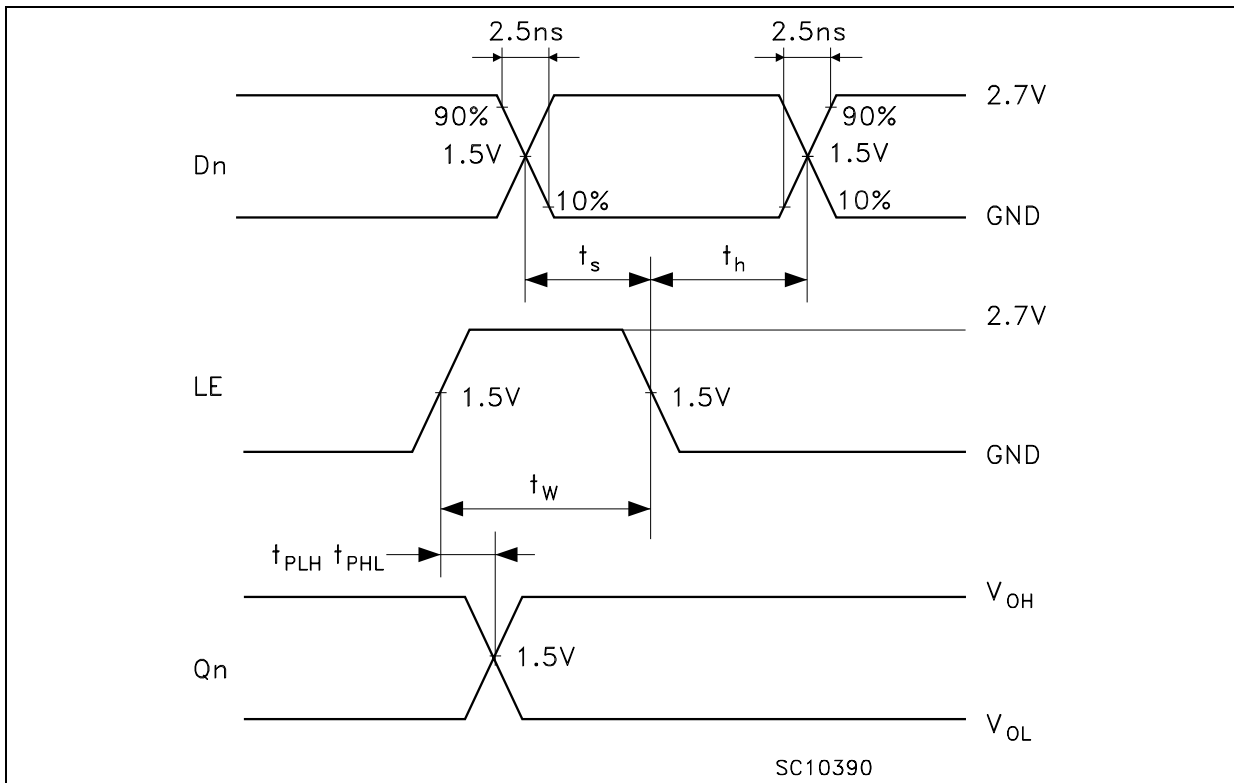
TEST CIRCUIT

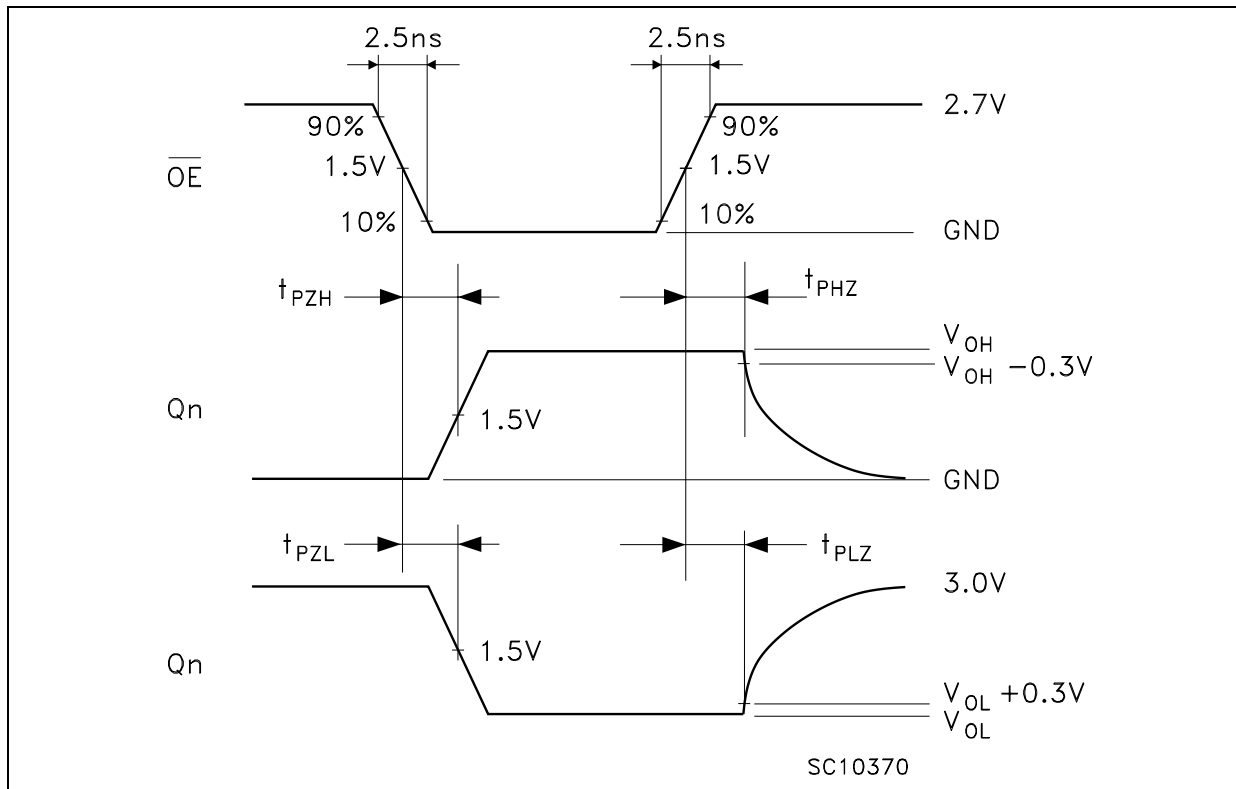
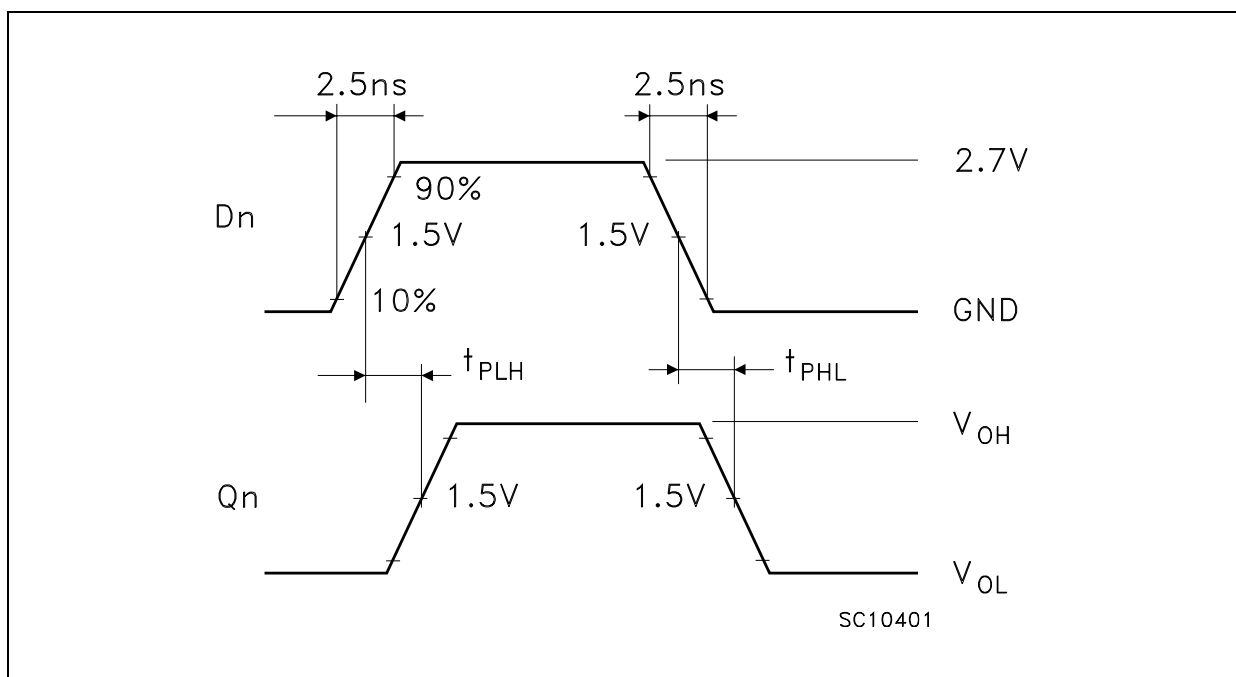


TEST	SWITCH
t_{PLH} , t_{PHL}	Open
t_{PZL} , t_{PLZ}	6V
t_{PZH} , t_{PHZ}	GND

C_L = 50 pF or equivalent (includes jig and probe capacitance)
 R_L = R_1 = 500 Ω or equivalent
 R_T = Z_{OUT} of pulse generator (typically 50 Ω)

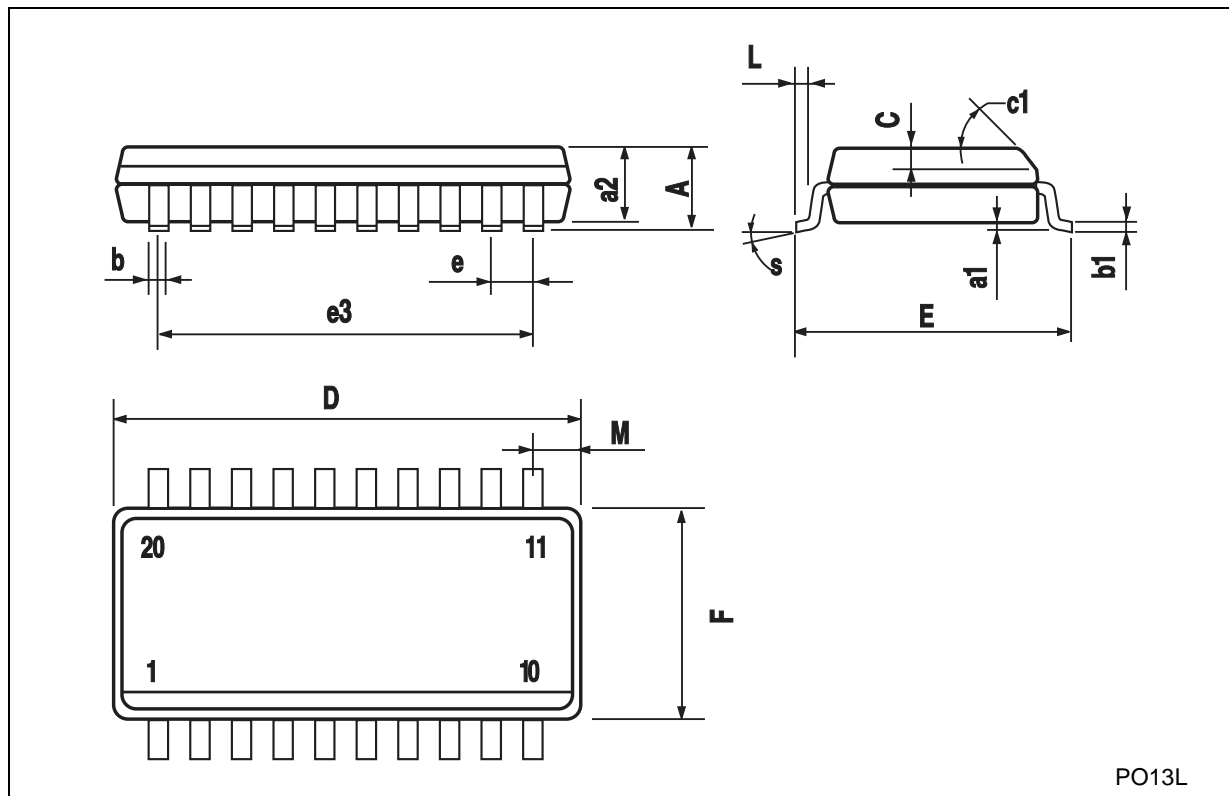
WAVEFORM 1 : LE TO Qn PROPAGATION DELAYS, LE PULSE WIDTH, Dn TO LE SETUP AND HOLD TIMES (f=1MHz; 50% duty cycle)



WAVEFORM 2 : OUTPUT ENABLE AND DISABLE TIMES (f=1MHz; 50% duty cycle)**WAVEFORM 3 : PROPAGATION DELAY TIME** (f=1MHz; 50% duty cycle)

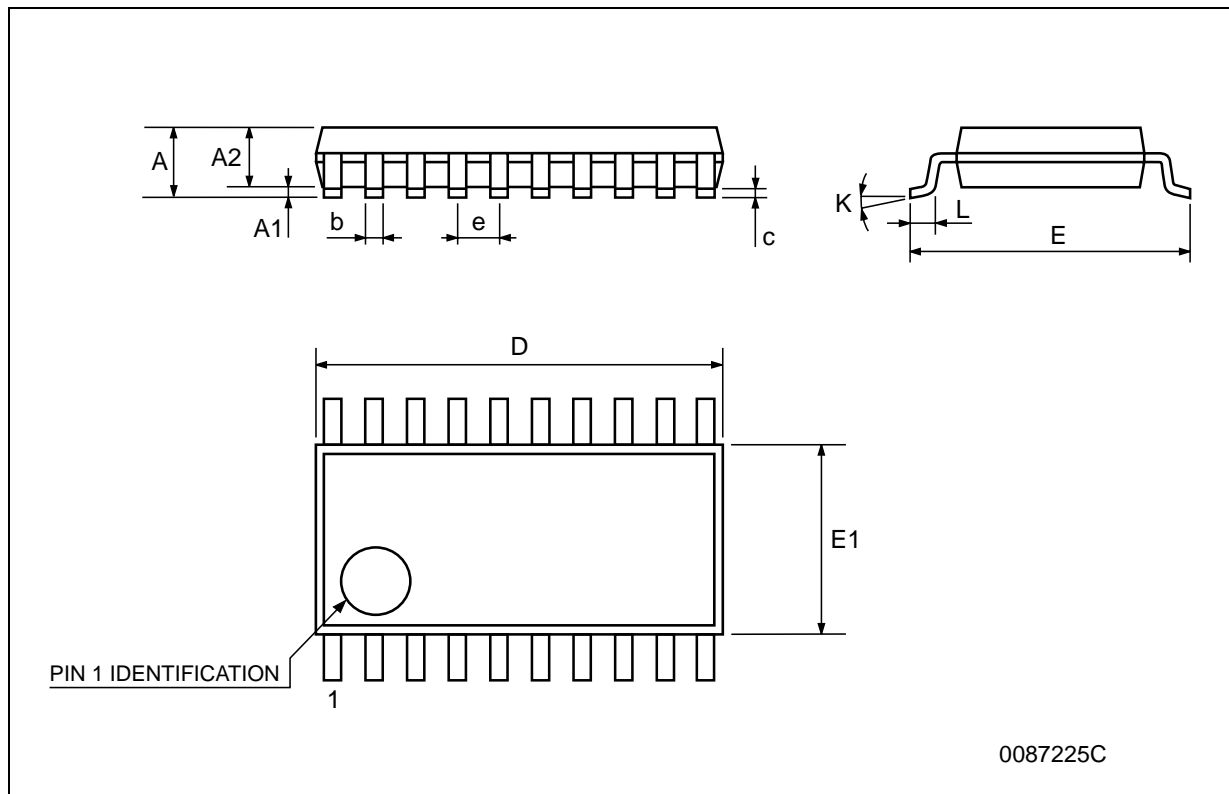
SO-20 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			2.65			0.104
a1	0.1		0.2	0.004		0.008
a2			2.45			0.096
b	0.35		0.49	0.014		0.019
b1	0.23		0.32	0.009		0.012
C		0.5			0.020	
c1	45° (typ.)					
D	12.60		13.00	0.496		0.512
E	10.00		10.65	0.393		0.419
e		1.27			0.050	
e3		11.43			0.450	
F	7.40		7.60	0.291		0.300
L	0.50		1.27	0.020		0.050
M			0.75			0.029
S	8° (max.)					



TSSOP20 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.0089
D	6.4	6.5	6.6	0.252	0.256	0.260
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



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